



Bipolar PNP Bare Die – BTP6960

Part Description

The BTP6960 is a silicon BJT transistor available in bare die form and well suited for use in general purpose switching and amplifier applications.

Key Parameters:

- VCBO = -140V
- VCEO = -100V
- VEBO = -7V
- hFE = 120-360 @ VCE = -2V, IC = -0.5A
- VCE(Sat) = -0.25V @ IC = -2A, IB = -200mA
- fT = 120 MHz @ VCE = -5V, IE = 0A
- COBO = 22pF @ VCB = -10V

Features

Very Low VCE(sat). Designed to provide performance equivalent to ONS NSS1C200L

Die Size (Unawn)

1010 μ m X 1010 μ m, 40 Mils X 40 Mils

This is a shortform datasheet only

For the full datasheet

Please contact sales@siliconsupplies.com

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